

IN THE CLAIMS:

Please amend Claims 42, 46, 49, and 50 as shown below.

1 to 41. (Cancelled)

42. (Currently Amended) A photoelectric conversion device comprising:
an electron acceptive charge transfer region;
an electron donative charge transfer region;
a light absorption region for photoelectric conversion, existing between the
charge transfer regions; and
two electrode regions between which the charge transfer regions and the
light absorption region are positioned,
wherein the light absorption region is a semiconductor, and either of the
charge transfer regions is a semiconductor acicular crystal region comprising an aggregate
of acicular crystals, and
wherein the acicular crystals comprise a metal oxide.

43. (Cancelled)

44. (Previously Presented) A photoelectric conversion device according to
claim 42, wherein the metal oxide is titanium oxide, zinc oxide or tin oxide.

45. (Previously Presented) A photoelectric conversion device according to
claim 42, wherein an aspect ratio of the acicular crystals is 5 or more when the aspect ratio

is defined as the ratio of the length of the acicular crystals to the diameter of the acicular crystals or as the ratio of the length of the acicular crystals to the length of the shortest line in a transverse cross-section of the acicular crystals passing the gravity center of the acicular crystals.

46. (Currently Amended) A photoelectric conversion device according to claim 42, wherein the light absorption region comprises an amorphous semiconductor or a direct transition ~~type~~ semiconductor.

47. (Previously Presented) A photoelectric conversion device according to claim 42, wherein the acicular crystals bear particles.

48. (Previously Presented) A photoelectric conversion device according to claim 42, wherein the acicular crystals are joined to a surface of a substrate and the angle between the axial direction of the acicular crystals and the surface of the substrate is 60 degrees or more.

49. (Currently Amended) A photoelectric conversion device comprising:
an electron acceptive charge transfer region;
an electron donative charge transfer region;
a light absorption region for photoelectric conversion, existing between the charge transfer regions; and

two electrode regions between which the charge transfer regions and the light absorption region are positioned,

wherein the light absorption region is a semiconductor, and either of the charge transfer regions is a semiconductor acicular crystal region comprising an aggregate of acicular crystals, and

wherein the acicular crystals comprise CuI or NiO.

50. (Currently Amended) A photoelectric conversion device comprising:

an electron acceptive charge transfer region;

an electron donative charge transfer region;

a light absorption region for photoelectric conversion, existing between the charge transfer regions; and

two electrode regions between which the charge transfer regions and the light absorption region are positioned,

wherein the light absorption region is a semiconductor, and either of the charge transfer regions is a semiconductor acicular crystal region comprising an aggregate of acicular crystals, and

wherein an aspect ratio of the acicular crystals is 10 or more when the aspect ratio is defined as the ratio of the length of the acicular crystals to the diameter of the acicular crystals or as the ratio of the length of the acicular crystals to the length of the shortest line in a transverse cross-section of the acicular crystals passing the gravity center of the acicular crystals.